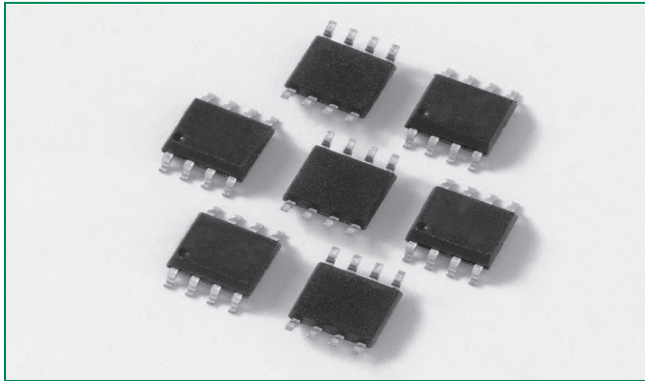
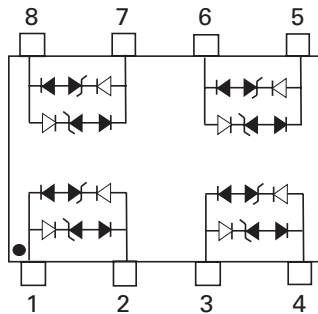


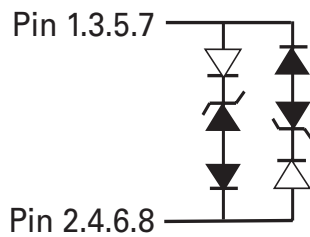
SLVU2.8-8 Series 2.8V 30A TVS Array



Pinout



Functional Block Diagram



Description

The SLVU2.8-8 was designed to protect low voltage, CMOS devices from ESD and lightning induced transients. There is a compensating diode in series with each low voltage TVS to present a low loading capacitance to the line being protected. These robust structures can safely absorb repetitive ESD strikes at $\pm 30\text{kV}$ (contact discharge) per IEC 61000-4-2 standard and can safely dissipate up to 30A (IEC 61000-4-5 2nd Edition, $t_p=8/20\mu\text{s}$) with very low clamping voltages.

Features

- ESD, IEC 61000-4-2, $\pm 30\text{kV}$ contact, $\pm 30\text{kV}$ air
- EFT, IEC 61000-4-4, 40A (5/50ns)
- Lightning, IEC 61000-4-5 2nd Edition, 30A (8/20 μs)
- Low capacitance of 2.6pF per line
- Low leakage current of 0.1 μA (MAX) at 2.8V
- SOIC-8 (JEDEC MO-012) pin configuration allows for protection of all 4 differential pair for 1GbE
- RoHS Compliant and Lead Free
- Moisture Sensitivity Level (MSL-1)

Applications

- 10/100/1000 Ethernet
- WAN/LAN Equipment
- Switching Systems
- Desktops, Servers, and Notebooks
- Analog Inputs
- Base Stations

Additional Information



Datasheet



Resources



Samples

Absolute Maximum Ratings

Parameter	Rating	Units
Peak Pulse Power ($t_p=8/20\mu s$)	750	W
Peak Pulse Current ($t_p=8/20\mu s$)	30	A
Operating Temperature	-40 to 125	°C
Storage Temperature	-55 to 150	°C

Thermal Information

Parameter	Rating	Units
Storage Temperature Range	-55 to 150	°C
Maximum Junction Temperature	150	°C
Maximum Lead Temperature (Soldering 20-40s)	260	°C

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

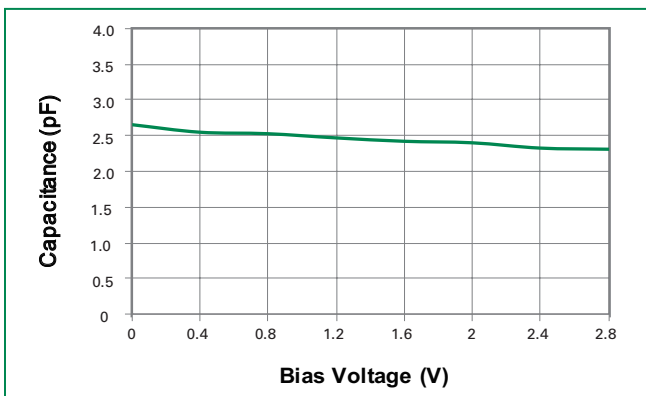
Electrical Characteristics ($T_{op} = 25^\circ C$)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Reverse Standoff Voltage	V_{RWM}	$I_r \leq 1\mu A$ (Each Line)			2.8	V
Reverse Breakdown Voltage	V_{BR}	$I_r = 2\mu A$ (Each Line)	3.0			V
Snapback Voltage	V_{SB}	$I_{SB} = 50mA$	2.8			V
Reverse Leakage Current	I_{LEAK}	$V_r = 2.8V$ (Each Line)			0.1	μA
Clamping Voltage ¹	V_C	$I_{PP} = 5A, t_p = 8/20\mu s$ (Each Line)			8.5	V
		$I_{PP} = 24A, t_p = 8/20\mu s$ (Each Line)			17	
ESD Withstand Voltage ¹	V_{ESD}	IEC61000-4-2 (Contact)	± 30			kV
		IEC61000-4-2 (Air)	± 30			
Dynamic Resistance ²	R_{DYN}	TLP $t_p = 100ns$, (Each Line)		0.3		Ω
Diode Capacitance ¹	C_D	$V_r = 0V, f = 1MHz$ (Each Line)		2.6	3.0	pF

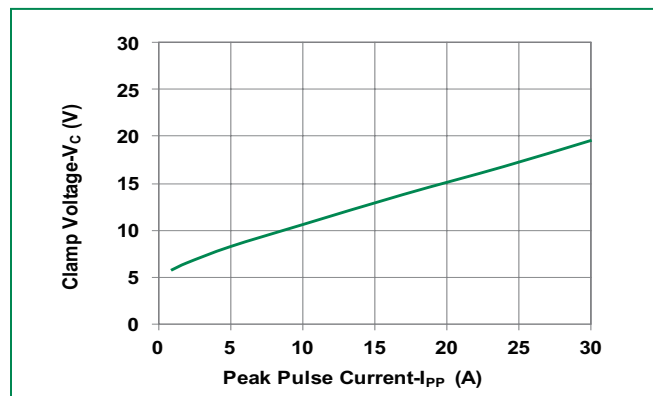
Note: 1 Parameter is guaranteed by design and/or device characterization.

2 Transmission Line Pulse (TLP) test setting : Std.TDR(50 Ω), $t_p = 100ns$, $t_r = 0.2ns$ ITLP and VTLP averaging window: star $t_1 = 70ns$ to end $t_2 = 80ns$

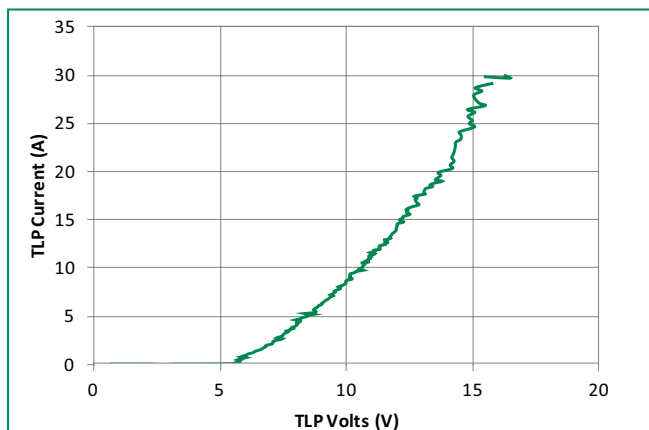
Capacitance vs. Reverse Bias (Each line)



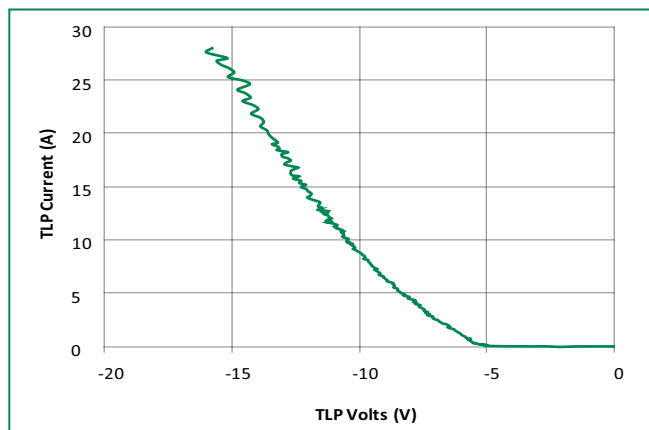
Clamping Voltage vs. Peak Pulse Current (Each line)



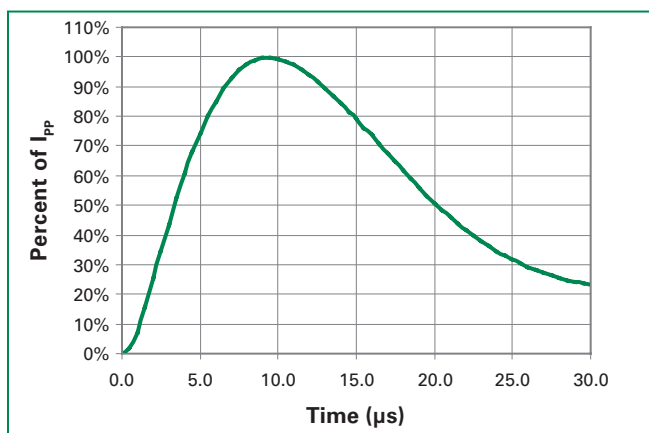
Positive Transmission Line Pulsing (TLP) Plot (Each line)



Negative Transmission Line Pulsing (TLP) Plot (Each line)



8/20 μs Pulse Waveform



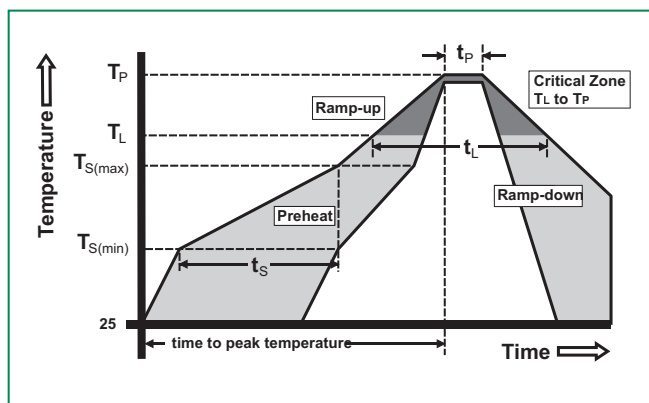
Product Characteristics

Lead Plating	Matte Tin
Lead Material	Copper Alloy
Lead Coplanarity	0.0004 inches (0.102mm)
Substrate material	Silicon
Body Material	V-0 per UL 94 Molded Epoxy

- Notes :
1. All dimensions are in millimeters
 2. Dimensions include solder plating.
 3. Dimensions are exclusive of mold flash & metal burr.
 4. All specifications comply to JEDEC SPEC MO-203 Issue A
 5. Blo is facing up for mold and facing down for trim/form, i.e. reverse trim/form.
 6. Package surface matte finish VDI 11-13.

Soldering Parameters

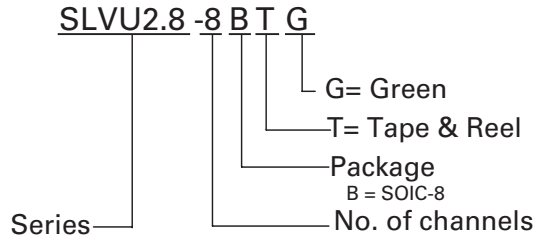
Reflow Condition		Pb – Free assembly
Pre Heat	- Temperature Min ($T_{s(min)}$)	150°C
	- Temperature Max ($T_{s(max)}$)	200°C
	- Time (min to max) (t_s)	60 – 180 secs
Average ramp up rate (Liquidus) Temp (T_L) to peak		5°C/second max
$T_{s(max)}$ to T_L - Ramp-up Rate		5°C/second max
Reflow	- Temperature (T_L) (Liquidus)	217°C
	- Temperature (t_L)	60 – 150 seconds
Peak Temperature (T_p)		260 ^{+0/-5} °C
Time within 5°C of actual peak Temperature (t_p)		20 – 40 seconds
Ramp-down Rate		5°C/second max
Time 25°C to peak Temperature (T_p)		8 minutes Max.
Do not exceed		260°C



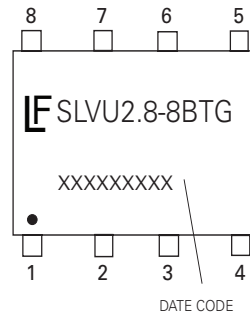
Ordering Information

Part Number	Package	Min. Order Qty.
SLVU2.8-8BTG	SOIC-8	2500

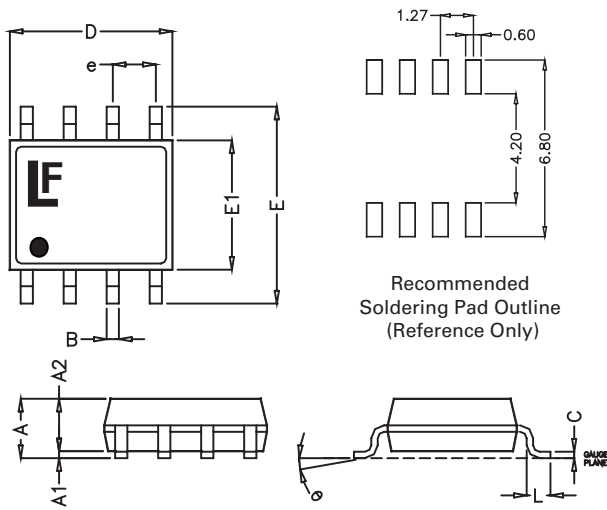
Part Numbering System



Part Marking System

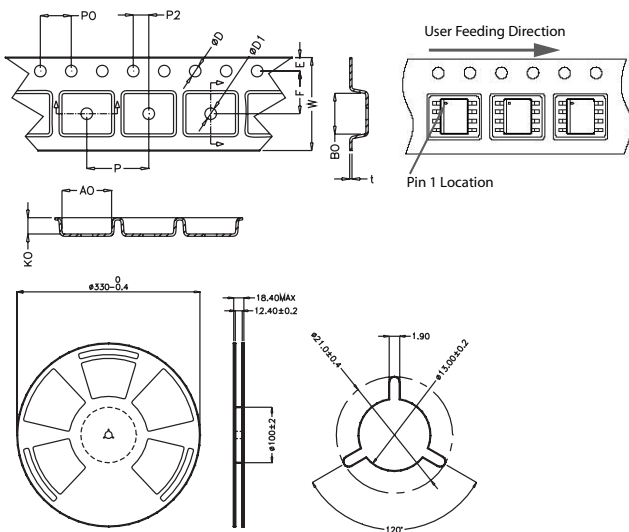


Package Dimensions – Mechanical Drawings and Recommended Solder Pad Outline



Package	SOIC-8			
Pins	8			
JEDEC	MS-012			
	Millimetres		Inches	
	Min	Max	Min	Max
A	1.35	1.75	0.053	0.069
A1	0.10	0.25	0.004	0.010
A2	1.25	1.65	0.050	0.065
B	0.31	0.51	0.012	0.020
c	0.17	0.25	0.007	0.010
D	4.80	5.00	0.189	0.197
E	5.80	6.20	0.228	0.244
E1	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
L	0.40	1.27	0.016	0.050

Embossed Carrier Tape & Reel Specification – SOIC Package



Symbol	Millimetres		Inches	
	Min	Max	Min	Max
E	1.65	1.85	0.065	0.073
F	5.4	5.6	0.213	0.22
P2	1.9	2.1	0.075	0.083
D	1.5	1.6	0.059	0.063
D1	1.50 Min		0.059 Min	
P0	3.9	4.1	0.154	0.161
10P0	40.0 +/- 0.20		1.574 +/- 0.008	
W	11.9	12.1	0.468	0.476
P	7.9	8.1	0.311	0.319
A0	6.3	6.5	0.248	0.256
B0	5.1	5.3	0.2	0.209
K0	2	2.2	0.079	0.087
t	0.30 +/- 0.05		0.012 +/- 0.002	